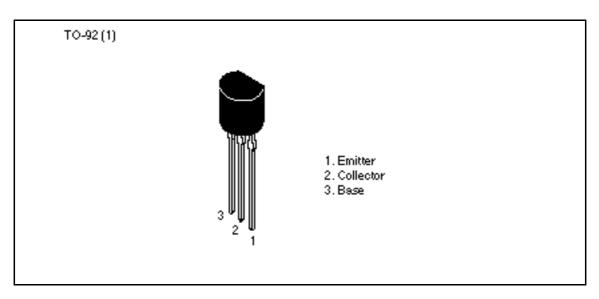
Silicon NPN Epitaxial

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Application

- Low frequency low noise amplifier
- Complementary pair with 2SA872/A

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	2SC1775	2SC1775A	Unit
Collector to base voltage	V _{cbo}	90	120	V
Collector to emitter voltage	V _{CEO}	90	120	V
Emitter to base voltage	V _{EBO}	5	5	V
Collector current	I _c	50	50	mA
Collector power dissipation	Pc	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	–55 to +150	–50 to +150	°C

Electrical Characteristics (Ta = 25° C)

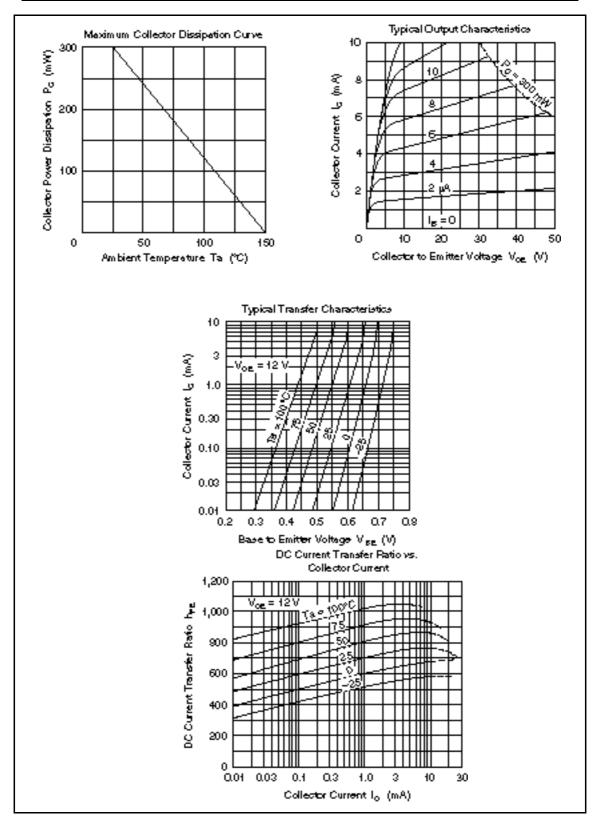
		2SC1	775		2SC1775A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	90	_		120	_		V	$I_c = 1 \text{ mA}, R_{BE} =$
Collector cutoff current	I _{CBO}	_	—	0.5		_	_	μA	$V_{CB} = 75 \text{ V}, \text{ I}_{E} = 0$
		_	_	_		_	0.5	μA	$V_{CB} = 100 \text{ V}, \text{ I}_{E} = 0$
DC current transfer ratio	$h_{\rm FE1}^{*1}$	400	_	1200	400	_	1200		V_{ce} = 12 V, I_c = 2 mA
	h_{FE2}	160	_	_	160	_	_		$V_{ce} = 12 \text{ V},$ $I_c = 0.1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	_	_	0.75	V	$V_{ce} = 12 \text{ V}, I_c = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$		_	0.5	_	_	0.5	V	$I_{c} = 10 \text{ mA}, I_{B} = 1 \text{ mA}$
Gain bandwidth product	f _T	_	200			200	_	MHz	V_{ce} = 12 V, I_c = 2 mA
Collector output capacitance	Cob	_	1.6	_	_	1.6		pF	$V_{CB} = 25 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise figure	NF		_	5.0	—		5.0	dB	$ \begin{array}{ll} V_{\rm CE} = 6 \ V, & f = 10 \\ I_{\rm C} = 50 \ \mu A, & Hz \\ R_{\rm g} = 50 \ k \end{array} $
		—	_	1.5	_	—	1.5	dB	f = 1 kHz

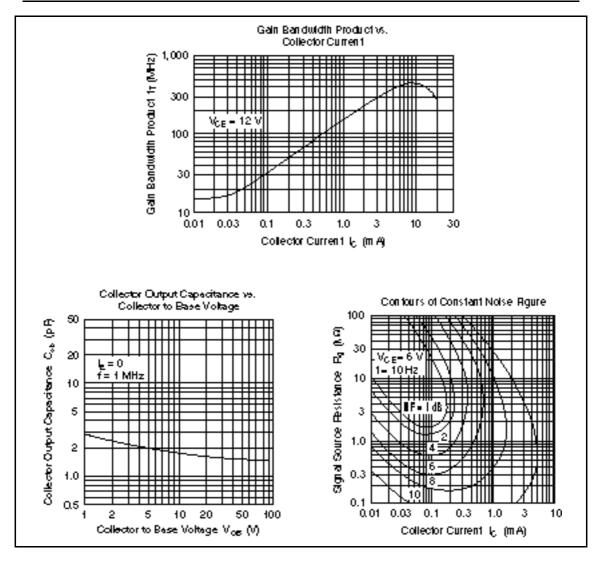
Note: 1. The 2SC1775/A is grouped by h_{FE1} as follows.

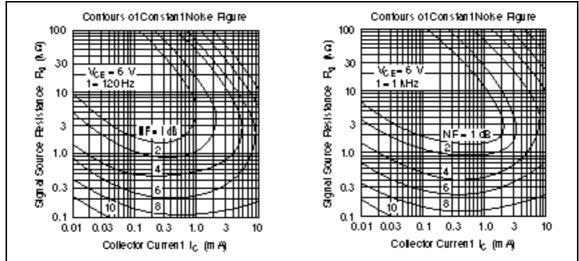
E F

400 to 800 600 to 1200









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